

DERWENT-ACC-NO: 1984-027629
DERWENT-WEEK: 198405
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TITLE: Carbon-silicon carbide composite mfr. - involves
selectively forming
carbide layer on carbon (J5 16.1.82)

PATENT-ASSIGNEE: HITACHI CHEM CO LTD[HITB]

PRIORITY-DATA: 1980JP-0079655 (June 12, 1980)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
JP 84001236 B	January 11, 1984	N/A
002	N/A	
JP 57007880 A	January 16, 1982	N/A
000	N/A	

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
JP 84001236B	N/A	1980JP-0079655
June 12, 1980		

INT-CL (IPC): C04B041/06

ABSTRACTED-PUB-NO: JP 84001236B

BASIC-ABSTRACT: Process comprises forming SiC layer on the
surface layer of
carbon substrate. A part where the formation of SiC layer
is not required has
porosity of less than 90% and is covered with fine powder
which is stable at
above 1500 deg.C, and then SiC treatment is carried out to
partially form SiC
layer. (J57007880-A)

CHOSEN-DRAWING: Dwg.0/0

TITLE-TERMS:

CARBON SILICON CARBIDE COMPOSITE MANUFACTURE SELECT FORMING
CARBIDE LAYER
CARBON

DERWENT-CLASS: L02

CPI-CODES: L02-A02A; L02-H02A; L02-H04; L02-J02C;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C1984-011986